

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	386257	((optical or laser or information) near5 (disc or disk or media or medium)).ti,ab.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/15 10:36
S2	14142	S1 and (spacer or ((intermediate or spacing or middle or separat\$4 or spac\$5) near3 (film or layer)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 10:37
S3	1365442	(spacer or ((intermediate or spacing or middle or separat\$4 or spac\$5) near3 (film or layer)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 10:38
S4	319475	((("2.0"\$1 or "2.1"\$1 or "2.1"\$1 or "2.3"\$1 or "2.4"\$1 or "2.5"\$1 or "2.6"\$1 or "2.7"\$1 or "2.8"\$1 or "2.9"\$1) near3 (micrometer or ".mu.m")) or (("200" or "210" or "220" or "230" or "240" or "250" or "260" or "270" or "280" or "290" or "300") near3 (nm or nanometer)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 10:41
S5	77283	S4 with thickness	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 10:42
S6	5009	S5 same S3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 10:43

S7	236	S6 and S1	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 10:43
S8	159	S7 and @ad<"20050627"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 10:43
S9	204	S7 and @ad<"20060627"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 10:43
S10	3	"20050025000"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 11:05
S11	2	"20050025000" and ".5"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 11:06
S12	2	"20060246360"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:05
S13	1	"20060246360" and "120"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:05
S14	2	"20060246360" and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:05
S15	247625	gate adj electrode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:14

S16	62565	S15 and ("gate insulating" near3 (film or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:14
S17	58322	S16 and (substrate or base)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:15
S18	5089	S17 and (buffer near2 (film or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:15
S19	4030	S18 and (semiconductor near3 (film or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:15
S20	2400	S19 and "drain electrode"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:15
S21	244	S20 and ((light near2 shielding) near3 (film or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:16
S22	144	S21 and @ad<"20060317"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:16
S23	5153078	(light-shielding or lightshielding) near3 film or layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:30
S24	198739	S23 with channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:30

S25	63186	S24 and "gate electrode"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:31
S26	25743	S25 and "drain electrode"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:31
S27	4329	S26 and (buffer near3 (film or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:31
S28	2097	S27 and ((gate-insulating or "gate insulating") near3 (film or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:32
S29	1709	S28 and (semiconductor near3 (film or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:33
S30	1657	S29 and (si or silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:33
S31	4900	((light near2 shielding) near3 (film or layer)) with (al or aluminum or mo or molybdenum or tantalum or ta or cr or chromium or cromium or ti ot titanium)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:34
S32	52	S30 and S31	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:34
S33	37	S32 and @ad< "20060317"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:35

S34	1	"20060246360" and buffer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 13:53
S35	2	"20060246360" and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 15:01
S36	2	"20060246360" and "display array"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 15:02
S37	1	"20060246360" and ("buffer layer" with material)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/15 15:07
S38	2	"20060246360" and ("B" or Boron)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/16 12:38
S39	0	"20060246360" and ion	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/16 12:38
S40	2	"20060246360" and doped	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/16 12:38
S41	2	"20060246360" and (gate near3 layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/16 12:40
S42	2	"20010008691"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/16 14:24

S43	2	"5609990".pn.	US-PGRUB; USPAT; USOQR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/16 14:25
S44	1	"20070059479" and aromatic	US-PGRUB; USPAT; USOQR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/16 14:33

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